

Matthias Wieneke

List of Publications by Year in descending order

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26
papers

300
citations

840776

11
h-index

839539

18
g-index

26
all docs

26
docs citations

26
times ranked

450
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Raman tensor determination of transparent uniaxial crystals and their thin films— α -plane GaN as exemplary case. Applied Physics Letters, 2021, 119, 121109. | 3.3 | 0 |
| 2 | The impurity size-effect and phonon deformation potentials in wurtzite GaN. Semiconductor Science and Technology, 2020, 35, 095033. | 2.0 | 4 |
| 3 | Impact of AlN/Si Nucleation Layers Grown Either by NH_3 -MBE or MOCVD on the Properties of AlGaIn/GaN HFETs. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700638. | 1.8 | 0 |
| 4 | Valence band tomography of wurtzite GaN by spectroscopic ellipsometry. Applied Physics Express, 2018, 11, 101001. | 2.4 | 10 |
| 5 | Observation of individual stacking faults in GaN microcrystals by x-ray nanodiffraction. Applied Physics Letters, 2017, 110, . | 3.3 | 6 |
| 6 | Leakage currents and Fermi-level shifts in GaN layers upon iron and carbon-doping. Journal of Applied Physics, 2017, 122, . | 2.5 | 23 |
| 7 | Nanoscale cathodoluminescence of stacking faults and partial dislocations in α -plane GaN. Physica Status Solidi (B): Basic Research, 2016, 253, 73-77. | 1.5 | 2 |
| 8 | Anisotropy of effective electron masses in highly doped nonpolar GaN. Applied Physics Letters, 2013, 103, . | 3.3 | 33 |
| 9 | Ge as a surfactant in metal-organic vapor phase epitaxy growth of α -plane GaN exceeding carrier concentrations of 10^{20} cm^{-3} . Applied Physics Letters, 2013, 103, . | 3.3 | 18 |
| 10 | Optical characterization of a InGaIn/GaN microcavity with epitaxial AlInN/GaN bottom DBR. Materials Research Society Symposia Proceedings, 2012, 1396, . | 0.1 | 0 |
| 11 | Optical anisotropy of α -plane $\text{Al}_{0.8}\text{In}_{0.2}\text{N}$ grown on an α -plane GaN pseudosubstrate. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 29-32. | 1.8 | 0 |
| 12 | Growth and coalescence behavior of semipolar $(11\bar{2})$ GaN on pre-structured α -plane sapphire substrates. Physica Status Solidi (B): Basic Research, 2011, 248, 588-593. | 1.5 | 34 |
| 13 | Heavy Si doping: The key in heteroepitaxial growth of α -plane GaN without basal plane stacking faults?. Physica Status Solidi (B): Basic Research, 2011, 248, 578-582. | 1.5 | 17 |
| 14 | Unintentional doping of α -plane GaN by insertion of in situ SiN masks. Journal Physics D: Applied Physics, 2011, 44, 085102. | 2.8 | 1 |
| 15 | Eliminating stacking faults in semi-polar GaN by AlN interlayers. Applied Physics Letters, 2011, 99, 021905. | 3.3 | 22 |
| 16 | Metalorganic vapor-phase epitaxy of GaN layers on Si substrates with Si(110) and other high-index surfaces. Journal of Crystal Growth, 2010, 312, 180-184. | 1.5 | 17 |
| 17 | Optical anisotropy of A - and M -plane InN grown on free-standing GaN substrates. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1062-1065. | 1.8 | 15 |
| 18 | Valence-band splitting and optical anisotropy of AlN. Physica Status Solidi (B): Basic Research, 2010, 247, 1679-1682. | 1.5 | 26 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | Direct microscopic correlation of crystal orientation and luminescence in spontaneously formed nonpolar and semipolar GaN growth domains. Applied Physics Letters, 2010, 96, . | 3.3 | 6 |
| 20 | X-ray Study of Step Induced Lateral Correlation Lengths in Thin AlGa _N Nucleation Layers. Japanese Journal of Applied Physics, 2010, 49, 025503. | 1.5 | 0 |
| 21 | InGa _N /Ga _N light-emitting diodes on Si(111) substrates grown by metal-organic vapour phase epitaxy. Journal Physics D: Applied Physics, 2009, 42, 055107. | 2.8 | 35 |
| 22 | Microstructural anisotropy of a-plane GaN analyzed by high resolution X-ray diffraction. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S498. | 0.8 | 12 |
| 23 | Characterization of defects in undoped non c-plane and high resistance GaN layers dominated by stacking faults. Physica B: Condensed Matter, 2009, 404, 4922-4924. | 2.7 | 7 |
| 24 | Influence of anisotropic strain on excitonic transitions in a-plane GaN films. Microelectronics Journal, 2009, 40, 322-324. | 2.0 | 10 |
| 25 | High-overtone bulk acoustic wave resonator on galliumnitride. , 2009, , . | | 0 |
| 26 | a-plane GaN Shear Wave Thin Film Resonator. Frequency Control Symposium and Exhibition, Proceedings of the IEEE International, 2007, , . | 0.0 | 2 |